



HBZX55C Series

ZENER DIODES

Device Type	Nominal Zener Voltage V_z at I_{zt}^* (V)	Test Current I_{zT} (mA)	Maximum Zener Impedance		Typical Temperature Coefficient (%/°C)	Maximum Reverse Leakage Current		Maximum Regulator Current I_{zM} (mA)
			Z_{zT} at I_{zT} (Ω)	Z_{zk} at $I_{zk}=1mA$ (Ω)		I_R (uA)	Test-Voltage suffix B (V)	
HBZX55C2V4	2.28-2.56	5	85	600	-0.070	50	1.0	150
HBZX55C2V7	2.5-2.9	5	85	600	-0.070	10	1.0	135
HBZX55C3V0	2.8-3.2	5	85	600	-0.070	4	1.0	125
HBZX55C3V3	3.1-3.5	5	85	600	-0.065	2	1.0	115
HBZX55C3V6	3.4-3.8	5	85	600	-0.060	2	1.0	105
HBZX55C3V9	3.7-4.1	5	85	600	-0.050	2	1.0	95
HBZX55C4V3	4.0-4.6	5	75	600	-0.025	1	1.0	90
HBZX55C4V7	4.4-5.0	5	60	600	-0.010	0.5	1.0	85
HBZX55C5V1	4.8-5.4	5	35	550	+0.015	0.1	1.0	80
HBZX55C5V6	5.2-6.0	5	25	450	+0.025	0.1	1.0	70
HBZX55C6V2	5.8-6.6	5	10	200	+0.035	0.1	2.0	64
HBZX55C6V8	6.4-7.2	5	8	150	+0.045	0.1	3.0	58
HBZX55C7V5	7.0-7.9	5	7	50	+0.050	0.1	5.0	53
HBZX55C8V2	7.7-8.7	5	7	50	+0.050	0.1	6.0	47
HBZX55C9V1	8.5-9.6	5	10	50	+0.060	0.1	7.0	43
HBZX55C10	9.4-10.6	5	15	70	+0.070	0.1	7.5	40
HBZX55C11	10.4-11.6	5	20	70	+0.070	0.1	8.5	36
HBZX55C12	11.4-12.7	5	20	90	+0.070	0.1	9.0	32
HBZX55C13	12.4-14.1	5	26	110	+0.070	0.1	10	29
HBZX55C15	13.8-15.6	5	30	110	+0.070	0.1	11	27
HBZX55C16	15.3-17.1	5	40	170	+0.070	0.1	12	24
HBZX55C18	16.8-19.1	5	50	170	+0.070	0.1	14	21
HBZX55C20	18.8-21.2	5	55	220	+0.070	0.1	15	20
HBZX55C22	20.8-23.3	5	55	220	+0.070	0.1	17	18
HBZX55C24	22.8-25.6	5	80	220	+0.080	0.1	18	16
HBZX55C27	25.1-28.9	5	80	220	+0.080	0.1	20	14
HBZX55C30	28-32	5	80	220	+0.080	0.1	22	13
HBZX55C33	31-35	5	80	220	+0.080	0.1	24	12
HBZX55C36	34-38	5	80	220	+0.080	0.1	27	11
HBZX55C39	37-41	2.5	90	500	+0.080	0.1	30	10
HBZX55C43	40-46	2.5	90	600	+0.080	0.1	33	9.2
HBZX55C47	44-50	2.5	110	700	+0.080	0.1	36	8.5

Note : 1. Standard Voltage Tolerance is $\pm 5\%$ and Suffix "A" for $\pm 1\%$, Suffix "B" for $\pm 2\%$, Suffix "C" for $\pm 5\%$, Suffix "D" for $\pm 20\%$
2. *Measured With Pulses $T_p = 20m$ Sec.



Absolute Maximum Ratings

Characteristics	Symbol	Value	Unit
Zener Current see Table "Characteristics"			
Power Dissipation at Tamb=25°C	P _{tot}	500*	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _s	-65 to +175	°C

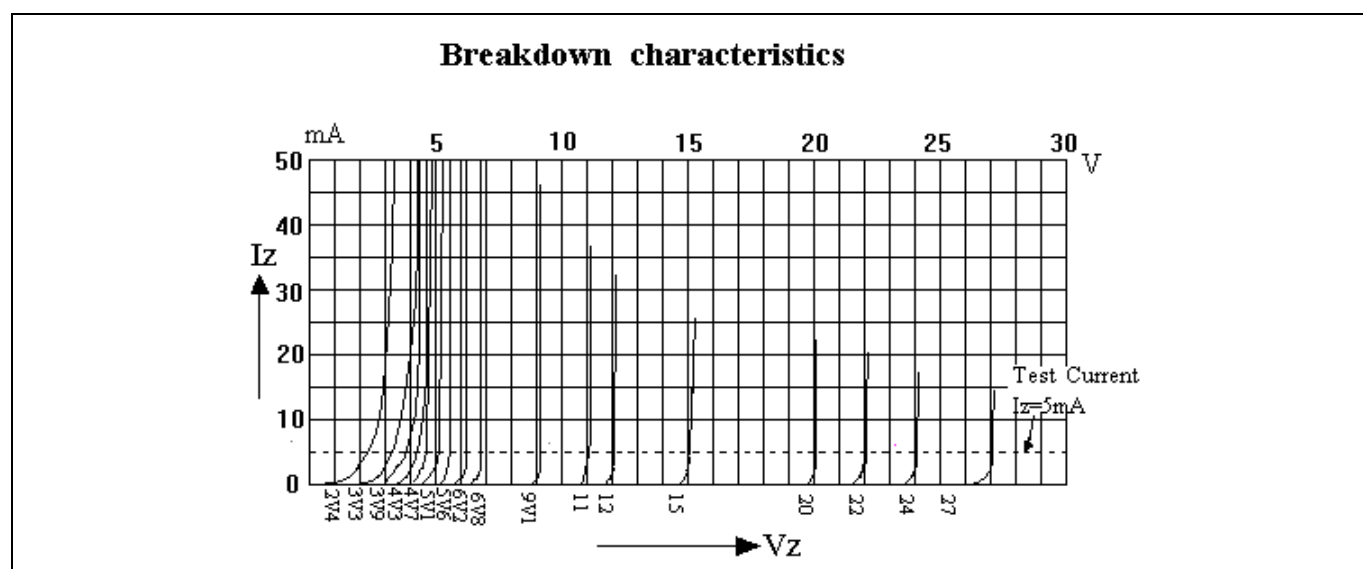
*Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.

Characteristics (Tamb=25°C)

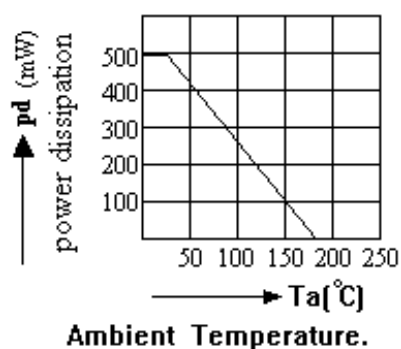
Characteristics	Symbol	Min	Typ	Max	Unit
Thermal Resistance Junction to Ambient Air	R _{thA}	-	-	0.3*	K/mW
Forward Voltage at I _F =100mA	V _F	-	-	1	V

*Valid provided that leads at a distance of 10mm from case are kept at ambient temperature.

Characteristics Curve

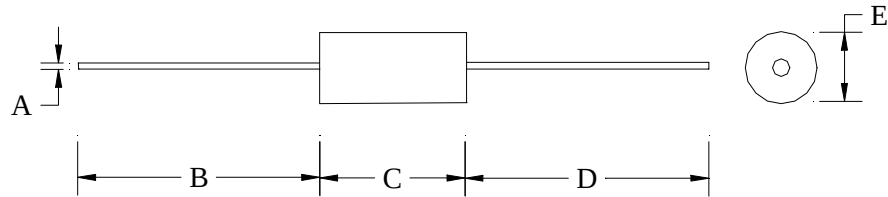


changes in the power dissipation
 due to the ambient temperature.





DO-35(Glass) Dimension



DO-35 Glasses Package, HSMC Package Code : L

*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	φ0.0181	φ0.0220	φ0.46	φ0.56	D	0.9646	1.2811	24.50	32.54
B	0.9646	1.2811	24.50	32.54	E	φ0.0602	φ0.0787	φ1.53	φ2.00
C	0.1200	0.1700	3.05	4.20					

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